

Discrete IGBTs Silicon N-Channel IGBT

GT30N135SRA

1. Applications

- · Dedicated to Voltage-Resonant Inverter Switching Applications
- · Dedicated to Soft Switching Applications
- · Dedicated to Induction Cooktops and Home Appliance Applications

Note: The product(s) described herein should not be used for any other application.

Note 1: This transistor is sensitive to electrostatic discharge and should be handled with care.

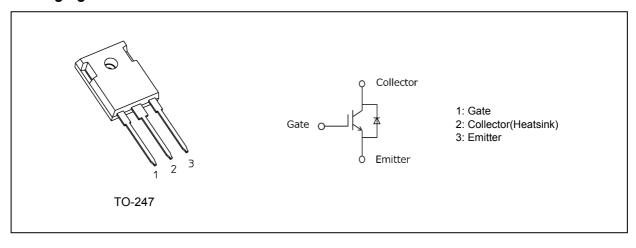
2. Features

- (1) 6.5th generation
- (2) The RC-IGBT consists of a freewheeling diode (FWD) monolithically integrated in an IGBT chip.
- (3) Enhancement mode
- (4) High-speed switching:

IGBT
$$t_f = 0.25 \mu s \text{ (typ.)} (I_C = 60 \text{ A})$$

- (5) Low saturation voltage: $V_{CE(sat)} = 1.65 \text{ V (typ.)}$ ($I_C = 30 \text{ A}$, $T_a = 25 ^{\circ}\text{C}$)
- (6) High junction temperature: $T_j = 175$ °C (max)

3. Packaging and Internal Circuit



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4. Absolute Maximum Ratings (Note) (T_a = 25 °C, unless otherwise specified)

Characteristics				Rating	Unit
Collector-emitter voltage		(Note 2)	V _{CES}	1350	V
Gate-emitter voltage			V _{GES}	±25	V
Collector current (DC)	(T _c = 25 °C)		Ic	60	Α
Collector current (DC)	(T _c = 100 °C)			30	
Collector current (1 ms)			I _{CP}	120	Α
Non-repetitive peak collector current		(Note 1)	I _{CSM}	260	Α
Diode forward current (DC)	(T _c = 25 °C)		I _F	60	Α
Diode forward current (DC)	(T _c = 100 °C)		1	30	
Diode forward current (100 μs)			I _{FP}	120	Α
Collector power dissipation	(T _c = 25 °C)		P _C	348	W
Junction temperature		(Note 2)	Tj	175	°C
Storage temperature			T _{stg}	-55 to 175	℃
Mounting torque			TOR	0.8	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

In general, loss of IGBT increases more when it has positive temperature coefficient and gets higher temperature.

In case that the temperature rise due to loss of IGBT exceeds the heat release capacity of a device, it leads to thermorunaway and results in destruction.

Therefore, please design heat release of a device with due consideration to the temperature rise of IGBT.

- Note 1: The maximum value of the capacitor charging current limited on T_i < 175 °C and t < 3 μ s
- Note 2: To perform derating ensures the device reliability.

In operation, the collector emitter voltage(V_{CES}) should be below 1150 V, as well as junction temperature(T_j) should be below 140 °C.

5. Thermal Characteristics

Characteristics		Symbol	Max	Unit
Jun	nction-to-case thermal resistance	R _{th(j-c)}	0.43	°C/W



6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25$ °C, unless otherwise specified)

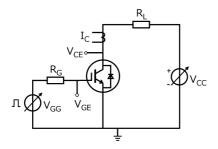
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GES}	$V_{GE} = \pm 25 \text{ V}, V_{CE} = 0 \text{ V}$	_	_	±100	nA
Collector cut-off current	I _{CES}	V _{CE} = 1350 V, V _{GE} = 0 V	_	_	100	μА
Collector-emitter breakdown voltage	V _{(BR)CES}	$I_C = 0.5 \text{ mA}, V_{GE} = 0 \text{ V}$	1350	_	_	V
Gate-emitter cut-off voltage	V _{GE(OFF)}	I _C = 60 mA, V _{CE} = 5 V	5.3	_	7.3	V
Collector-emitter saturation voltage	V _{CE(sat)(1)}	I _C = 30 A, V _{GE} = 15 V (pulse test)	_	1.65	1.95	V
	V _{CE(sat)(2)}	I _C = 30 A, V _{GE} = 15 V, T _c = 125 °C (pulse test)		1.90		
	V _{CE(sat)(3)}	I _C = 60 A, V _{GE} = 15 V (pulse test)	_	2.15	2.60	
	V _{CE(sat)(4)}	I _C = 60 A, V _{GE} = 15 V, T _c = 125 °C (pulse test)	_	2.60	_	
Diode forward voltage	V _{F(1)}	I _F = 30 A, V _{GE} = 0 V (pulse test)	_	1.75	2.40	V
	V _{F(2)}	$I_F = 30 \text{ A}, V_{GE} = 0 \text{ V},$ $T_c = 125 ^{\circ}\text{C} \text{ (pulse test)}$	_	1.85	_	



6.2. Dynamic Characteristics ($T_a = 25$ °C, unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{ies}	V _{CE} = 25 V, V _{GE} = 0 V,	_	3700	_	pF
Reverse transfer capacitance	C _{res}	f = 100 kHz	_	40	_	
Output capacitance	C _{oes}		_	55	_	
Total gate charge	Qg	V _{CE} = 600 V, I _C = 60 A, V _{GE} = 15 V	_	270	_	nC
Switching time (rise time)	t _r	Resistive load	_	0.14	_	μS
Switching time (turn-on time)	t _{on}	V_{CE} = 600 V, I_{C} = 60 A, V_{GE} = +15 V, R_{G} = 10 Ω	_	0.21	_	
Switching time (fall time)	t _f	See Fig. 6.2.1, 6.2.2	_	0.25	0.35	
Switching time (turn-off time)	t _{off}		_	0.50	_	
Switching loss (turn-off switching loss)	E _{off(1)}	Inductive load $V_{CE} = 300 \text{ V, } I_{C} = 60 \text{ A,} \\ V_{GE} = +15 \text{ V, } R_{G} = 39 \Omega \\ L = 30 \ \mu\text{H, } C = 0.33 \ \mu\text{F} \\ \text{See Fig. 6.2.3, 6.2.4}$	_	0.80	_	mJ
	E _{off(2)}	Inductive load $V_{CE} = 300 \text{ V, } I_{C} = 60 \text{ A,} \\ V_{GE} = +15 \text{ V, } R_{G} = 39 \Omega, \\ L = 30 \ \mu\text{H, } C = 0.33 \ \mu\text{F} \\ T_{c} = 125 \ ^{\circ}\text{C} \\ \text{See Fig. 6.2.3, 6.2.4}$	_	1.30	_	

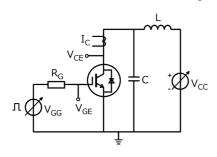
 V_{GE}



VCE 10% 10% 1 10% t 10%

Fig. 6.2.1 Test Circuit of Switching Time

Fig. 6.2.2 Timing Chart of Switching Time



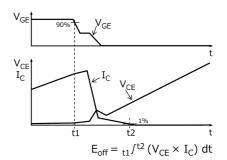


Fig. 6.2.3 Test Circuit of Switching Loss

Fig. 6.2.4 Timing Chart of Switching Loss

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Rev.1.0



7. Marking (Note)

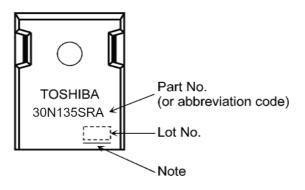


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

[[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

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8. Characteristics Curves (Note)

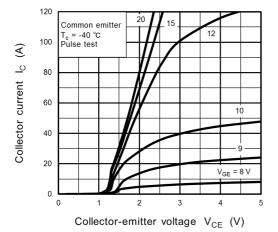
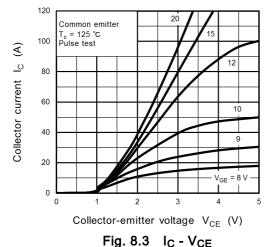
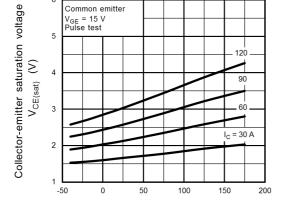


Fig. 8.1 I_C - V_{CE}





Case temperature T_c (°C) Fig. 8.5 $V_{CE(sat)}$ - T_c

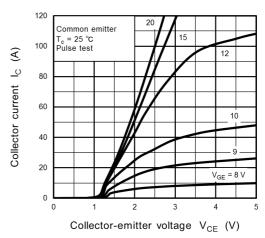


Fig. 8.2 I_C - V_{CE}

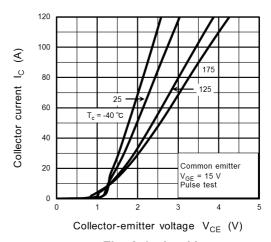


Fig. 8.4 Ic - VCE

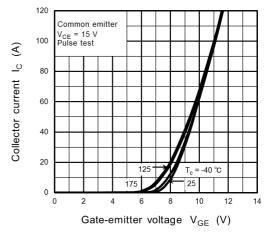


Fig. 8.6 Ic - VGE



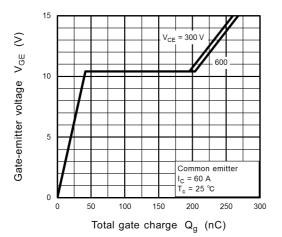


Fig. 8.7 V_{GE} - Q_g

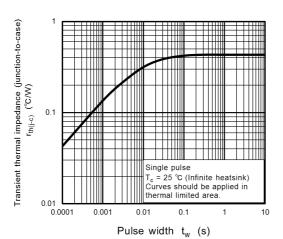


Fig. 8.9 $r_{th(j-c)} - t_w$ (Guaranteed Maximum)

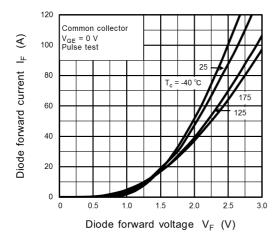


Fig. 8.11 I_F - V_F

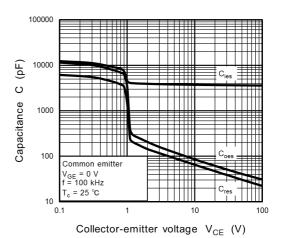


Fig. 8.8 C -V_{CE}

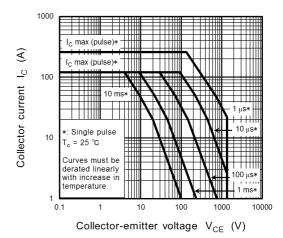


Fig. 8.10 Safe Operating Area (Guaranteed Maximum)

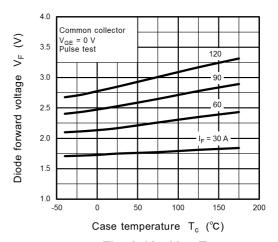


Fig. 8.12 V_F - T_c



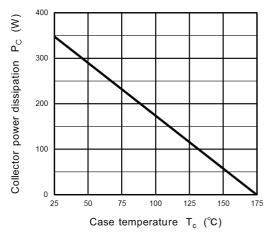


Fig. 8.13 Pc - Tc

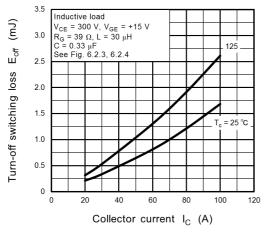


Fig. 8.15 E_{off} - I_C

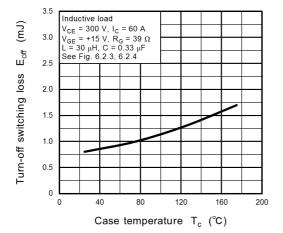


Fig. 8.17 E_{off} - T_c

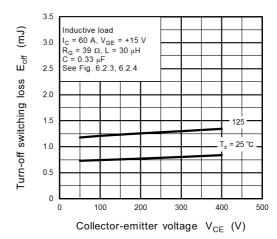


Fig. 8.14 Eoff - VCE

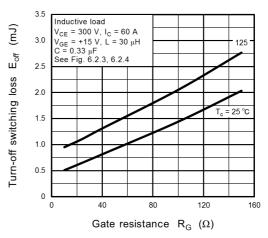


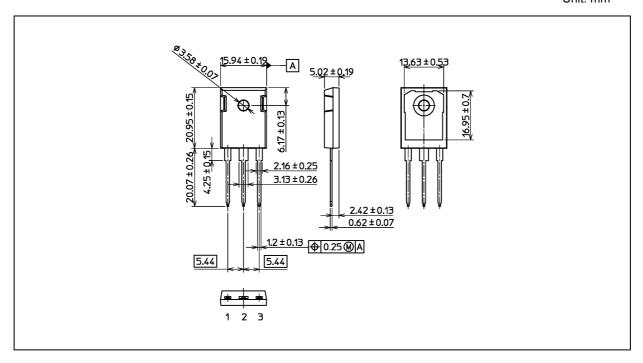
Fig. 8.16 E_{off} - R_G

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 6.15 g (typ.)

Package Name(s)
TOSHIBA: 2-16L1A
Nickname: TO-247



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